



**THE DATASHEET OF
ZVP0545ASTZ**



P-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

ISSUE 2 – MARCH 94

FEATURES

- * 450 Volt V_{DS}
- * $R_{DS(on)} = 150\Omega$

ABSOLUTE MAXIMUM RATINGS

PARAMETER
Drain-Source Voltage
Continuous Drain Current at $T_{amb}=25^{\circ}C$
Pulsed Drain Current
Gate Source Voltage
Power Dissipation at $T_{amb}=25^{\circ}C$
Operating and Storage Temperature Range

ELECTRICAL CHARACTERISTICS



PARAMETER	SYMBOL
Drain-Source Breakdown Voltage	BV_{DSS}
Gate-Source Threshold Voltage	$V_{GS(th)}$
Gate-Body Leakage Current	I_{GSS}
Zero Gate Voltage Drain Current	I_{DSS}
On-State Drain Current (1)	$I_{D(on)}$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$
Forward Transconductance (1)(2)	g_{fs}
Input Capacitance (2)	C_{iss}
Common Source Output Capacitance (2)	C_{oss}
Reverse Transfer Capacitance (2)	C_{rss}
Turn-On Delay Time (2)(3)	$t_{d(on)}$
Rise Time (2)(3)	t_r
Turn-Off Delay Time (2)(3)	$t_{d(off)}$
Fall Time (2)(3)	t_f

(1) Measured under pulsed conditions. $W_{eff} = 100\mu m$.

(2) Sample test.

Looking for pricing, stock, or lifecycle information?

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